# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



UHF power LDMOS transistor Rev. 2 — 30 August 2016

#### **Product profile** 1.

## 1.1 General description

A 750 W LDMOS RF power transistor for asymmetrical broadcast Doherty transmitter applications which operates at 150 W DVB-T average power. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

#### **Application information** Table 1.

RF performance at  $V_{DS}$  = 50 V in an asymmetrical Doherty application.

Test signal	f	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	IMD <sub>shldr</sub>	PAR
	(MHz)	(W)	(dB)	(%)	(dBc)	(dB)
DVB-T (8k OFDM)	470 to 608	150	17	52	-38	8 <u>[1]</u>
	600 to 700	150	17	50	-38	8 <u>[1]</u>
	650 to 790	150	15	49	-38	8 <u>[1]</u>

[1] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

## 1.2 Features and benefits

- Designed for asymmetric Doherty operation
- Very high efficiency enabling air cooled high power transmitters
- Integrated ESD protection
- Excellent ruggedness
- High power gain
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Broadcast transmitter applications in the UHF band
- Digital broadcasting

AMPLEON

# 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BLF888E	(SOT539A)		
1	drain1 (peak)		
2	drain2 (main)		
3	gate1 (peak)		
4	gate2 (main)	3 4	3 5
5	source	[1]	
			۲۳ ا
			2 sym117
BLF888E	S (SOT539B)		
1	drain1 (peak)		
2	drain2 (main)		
3	gate1 (peak)	5	
4	gate2 (main)		3 5
5	source	[1]	
			l IF-1
			2 sym117

[1] Connected to flange.

# 3. Ordering information

### Table 3.Ordering information

Type number	Packag	ackage				
	Name	Description	Version			
BLF888E	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLF888ES	-	earless flanged balanced ceramic package; 4 leads	SOT539B			

# 4. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS(amp)main</sub>	main amplifier drain-source voltage		-	104	V
V <sub>DS(amp)peak</sub>	peak amplifier drain-source voltage		-	120	V
V <sub>GS(amp)main</sub>	main amplifier gate-source voltage		-0.5	+11	V
V <sub>GS(amp)peak</sub>	peak amplifier gate-source voltage		-6	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

Product data sheet

# 5. Thermal characteristics

Table 5.	Thermal	characteristics
	i norman	onaraotoriotioo

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case} = 90 \ ^{\circ}C; \ V_{DS} = 50 \ V; $ [1] $I_{DS} = 3 \ A \ (main); \ I_{DS} = 0 \ A \ (peak)$	0.29	K/W
		T <sub>case</sub> = 90 °C; V <sub>DS</sub> = 50 V; [2] P <sub>L</sub> = 150 W; PAR = 8 dB	0.19	K/W

[1] Measured under DC test conditions, with peak section off.

[2] Measured in an ultra-wide Doherty application, using DVB-T (8k OFDM) signal, PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

# 6. Characteristics

### Table 6. DC characteristics

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Main dev	rice	1				-
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 2.4 mA	104	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 240 mA	1.25	1.75	2.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	2.8	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	38	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V	-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I <sub>D</sub> = 8.5 A	-	120	-	mΩ
Peak dev	vice	1				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 3.6 mA	125	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 360 mA	1.33	1.83	2.33	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	2.8	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	57	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V	-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I <sub>D</sub> = 12.6 A	-	90	-	mΩ

### Table 7.AC characteristics

 $T_j$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main device						
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	210	-	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	67	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	1.35	-	pF

### Table 7. AC characteristics ...continued

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Peak device						
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	315	-	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	105	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	1.5	-	pF

### Table 8. RF characteristics

*RF* characteristics in Ampleon production test circuit,  $T_{case} = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
DVB-T (8	DVB-T (8k OFDM), Doherty operation							
V <sub>DS</sub>	drain-source voltage		-	50	-	V		
I <sub>Dq</sub>	quiescent drain current	peak section: $V_{GS}$ = 1.3 V below $V_{GS(th)}$ (peak)	-	600	-	mA		
P <sub>L(AV)</sub>	average output power	f = 550 MHz	-	150	-	W		
G <sub>p</sub>	power gain	f = 550 MHz	15.8	17	-	dB		
$\eta_D$	drain efficiency	f = 550 MHz	48	52	-	%		
PAR	peak-to-average ratio	f = 550 MHz	7.2	7.8	-	dB		

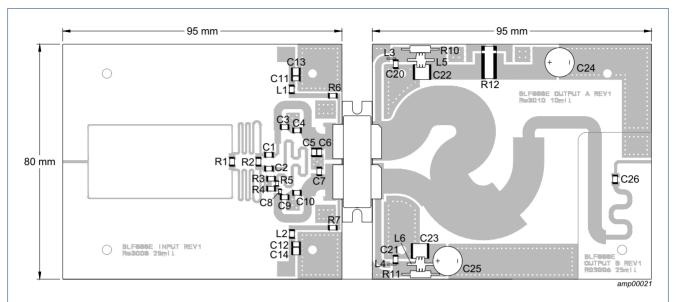
# 7. Test information

### 7.1 Ruggedness in Doherty operation

The BLF888E and BLF888ES are capable of withstanding a load mismatch corresponding to VSWR  $\ge$  40 : 1 through all phases under the following conditions: V<sub>DS</sub> = 50 V; f = 550 MHz at rated load power.

**UHF power LDMOS transistor** 

### 7.2 Test circuit



Printed-Circuit Board (PCB): Rogers 3006;  $\varepsilon_r$  = 6.5 F/m; height = 0.635 mm; Cu (top/bottom metalization); thickness copper plating = 29.6  $\mu$ m; Rogers 3010:  $\epsilon_r$  = 10 F/m; height = 0.254 mm

See Table 9 for a list of components.

#### Component layout for production RF test circuit Fig 1.

#### Table 9. List of components

For test circuit see <u>Figure 1</u> .					
Component	Description	Value		Remarks	
C1, C2	multilayer ceramic chip capacitor	51 pF	<u>[1]</u>	ATC 100B	
C3	multilayer ceramic chip capacitor	11 pF	<u>[1]</u>	ATC 100B	
C4	multilayer ceramic chip capacitor	13 pF	<u>[1]</u>	ATC 100B	
C5, C6	multilayer ceramic chip capacitor	24 pF	<u>[1]</u>	ATC 100B	
C7	multilayer ceramic chip capacitor	33 pF	<u>[1]</u>	ATC 100B	
C8	multilayer ceramic chip capacitor	51 pF	[2]	ATC 100A	
C9	multilayer ceramic chip capacitor	12 pF	<u>[1]</u>	ATC 100B	
C10	multilayer ceramic chip capacitor	20 pF	<u>[1]</u>	ATC 100B	
C11, C12	multilayer ceramic chip capacitor	43 pF	<u>[1]</u>	ATC 100B	
C13, C14	multilayer ceramic chip capacitor	4.7 μF			
C20, C21	electrolytic capacitor	100 pF	<u>[1]</u>	ATC 100B	
C22, C23	multilayer ceramic chip capacitor	4.7 μF, 100 V			
C25, C25	electrolytic capacitor	470 μF, 63 V			
C26	multilayer ceramic chip capacitor	47 pF	<u>[1]</u>	ATC 100B	
L1, L2	inductor	10 nH		Coilcraft	
L3, L4	inductor	0.5 turn, D = 2 mm, d = 1mm			
L5, L6	inductor	1 turn, D = 5 mm, d = 1mm			
R1	chip resistor	90 Ω			

### For test circuit see Figure 1 (

All information provided in this document is subject to legal disclaimers.

### Table 9. List of components ...continued

ron test chicuit see <u>rigure r</u> .						
Component	Description	Value	Remarks			
R2	chip resistor	265 Ω				
R3, R4	chip resistor	360 Ω				
R5	chip resistor	15 Ω				
R6	chip resistor	75 Ω				
R7	chip resistor	5 Ω				
R10, R11	wire resistor	1 Ω				
R12	shunt resistor	0.01 Ω				

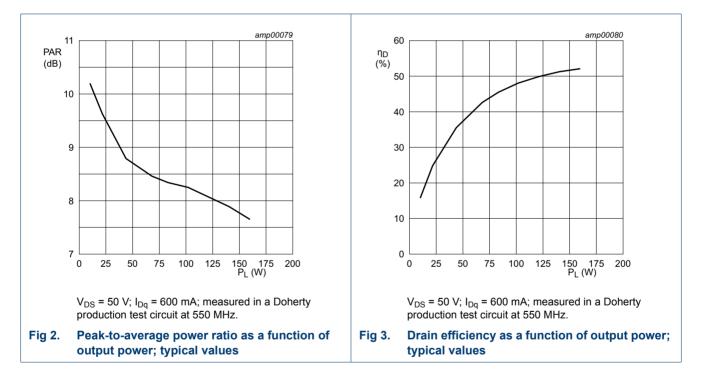
For test circuit see Figure 1.

[1] American Technical Ceramics type 100B or capacitor of same quality

[2] American Technical Ceramics type 100A or capacitor of same quality

### 7.3 Graphical data

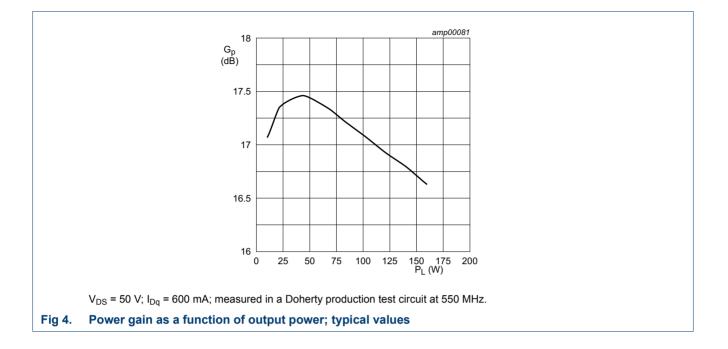
### 7.3.1 DVB-T in production test circuit



# AMPLEON

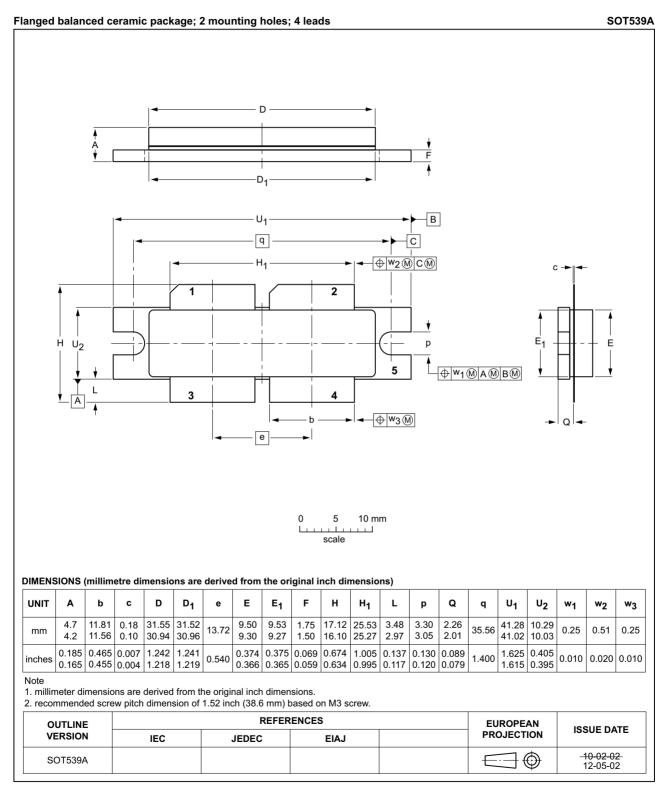
# BLF888E; BLF888ES

### **UHF power LDMOS transistor**



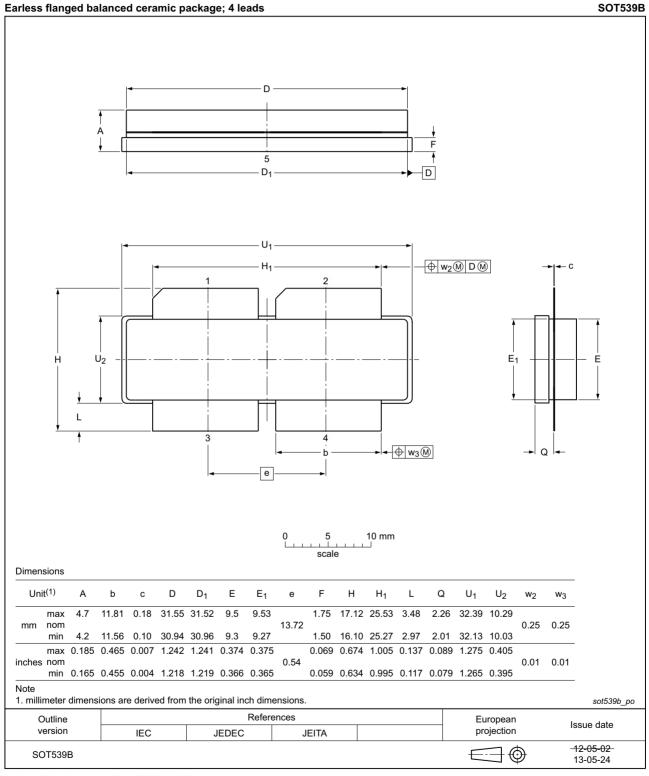
### UHF power LDMOS transistor

# 8. Package outline



### Fig 5. Package outline SOT539A

### **UHF power LDMOS transistor**



### Fig 6. Package outline SOT539B

BLF888E\_BLF888ES

# 9. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

# **10. Abbreviations**

Table 10. Abbreviations					
Acronym	Description				
CCDF	Complementary Cumulative Distribution Function				
DVB-T	Digital Video Broadcast - Terrestrial				
ESD	ElectroStatic Discharge				
LDMOS	Laterally Diffused Metal-Oxide Semiconductor				
MTF	Median Time to Failure				
OFDM	Orthogonal Frequency Division Multiplexing				
PAR	Peak-to-Average Ratio				
UHF	Ultra High Frequency				
VSWR	Voltage Standing Wave Ratio				

# 11. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BLF888E_BLF888ES v.2	20160830	Product data sheet	-	BLF888E_BLF888ES v.1		
Modifications:	<u>Section 1.1 on page 1</u> : section updated					
	Table 1 on p	age 1: table updated				
	<ul> <li><u>Section 1.2 on page 1</u>: text second list item updated</li> </ul>					
	• <u>Table 5 on page 3</u> : table updated					
	• <u>Table 6 on page 3</u> : table updated					
	<u>Table 8 on page 4</u> : table updated					
	<u>Section 7.1 on page 4</u> : section updated					
	<u>Section 7.3 on page 6</u> : section added					
BLF888E_BLF888ES v.1	20160317	Objective data sheet	-	-		

# 12. Legal information

## 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.ampleon.com">http://www.ampleon.com</a>.

## 12.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

## 12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

**Right to make changes** — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an

Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer's third party customer's hird party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.ampleon.com/terms">http://www.ampleon.com/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**UHF power LDMOS transistor** 

**Non-automotive qualified products** — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon' standard warranty and Ampleon' product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

### 12.4 Licenses

#### ICs with DVB-T or DVB-T2 functionality

Use of this product in any manner that complies with the DVB-T or the DVB-T2 standard may require licenses under applicable patents of the DVB-T respectively the DVB-T2 patent portfolio, which license is available from Sisvel S.p.A., Via Sestriere 100, 10060 None (TO), Italy, and under applicable patents of other parties.

## 12.5 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own trademarks.

# **13. Contact information**

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

### UHF power LDMOS transistor

# 14. Contents

1	Product profile	. 1
1.1	General description	. 1
1.2	Features and benefits	. 1
1.3	Applications	. 1
2	Pinning information	. 2
3	Ordering information	. 2
4	Limiting values	. 2
5	Thermal characteristics	. 3
6	Characteristics	. 3
7	Test information	. 4
7.1	Ruggedness in Doherty operation	. 4
7.2	Test circuit	. 5
7.3	Graphical data	. 6
7.3.1	DVB-T in production test circuit	. 6
8	Package outline	. 8
9	Handling information	10
10	Abbreviations	10
11	Revision history	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Licenses	12
12.5	Trademarks	12
13	Contact information	12
14	Contents	13

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

#### © Ampleon Netherlands B.V. 2016.

For more information, please visit: http://www.ampleon.com For sales office addresses, please visit: http://www.ampleon.com/sales

Date of release: 30 August 2016 Document identifier: BLF888E\_BLF888ES

All rights reserved.